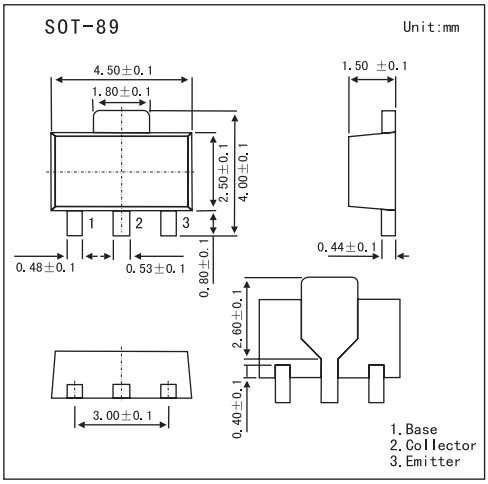
Medium Power Transistor

2SD2391



■ Features

- Low saturation voltage.
- Collector-emitter voltage =60V.
- PC=2 W (on 40×40×0.7mm ceramic board) .

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	60	V
Collector-emitter voltage	V_{CEO}	60	V
Emitter-base voltage	V_{EBO}	6	V
Collector current	I_C	2	A
Collector power dissipation	P_C	0.5	W
Junction temperature	Tj	150	℃
Storage temperature	T_{stg}	-55 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV_{CBO}	I_C=50μA	60			V
Collector-emitter breakdown voltage	BV_{CEO}	I_C=1mA	60			V
Emitter-base breakdown voltage	BV_{EBO}	I_E=50μA	6			V
Collector cutoff current	I_{CBO}	V_{CB}=50V			0.1	μA
Emitter cutoff current	I_{EBO}	V_{EB}=5V			0.1	μA
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=1A, I_B=50mA		0.13	0.35	V
DC current transfer ratio	h_{FE}	V_{CE}=-2V, I_C=-0.5A	120		270	
Output capacitance	f_T	V_{CE}=2V, I_E= -0.5A, f=100MHz		210		MHz
Transition frequency	C_{ob}	V_{CB}=10V, I_E=0A, f=1MHz		21		pF

■ Marking

Marking	DTQ